VLN Deep Silicon Etch System Specifications

DSE IV PROCESS SPECIFICATION

Parameter	DSE IV Specification
Si Etch Rate (µm/min)	≥7.5
Etch Depth	350 µm
CD size	1020 x 1020 µm
Aspect ratio	1:3
Si exposed area	~70%
Si: PR Selectivity	>100:1
Si: SiO_2 Selectivity	>150:1
Sidewall profile	90° ±2°
Sidewall roughness (µm)	<2
Within wafer Non-uniformity @ 6"	<±5% excluding edge exclusion 6mm